Influence of atomic level surface local structure on photo-induced oxidation reaction of water at single crystal TiO₂ surface

<u>Akihito Imanishi^{1*}</u>, Toshinori Sakao¹, Etsushi Tsuji², Ken-ichi Fukui¹

1) Department of Materials Engineering Science, Graduate School of Engineering Science, Osaka University, 560-8531, Japan, 2) Division of Materials Chemistry, Faculty of Engineering, Hokkaido University, Japan

We previously reported that the oxygen photoevolution reaction on TiO₂ surface is initiated by a nucleophilic attack of an H₂O molecule to a surface-trapped hole (STH), accompanied by bond breaking. On this process, the trapped holes were also extinguished by the other 3 kinds of processes (PL emission by recombination with electrons, non-radiative recombination and surface roughening reaction (i.e. surface etching)) besides the oxygen evolution reaction [1]. It was expected that the above 4 kinds of reactions occurs at different surface sites and are correlative with each other. This indicates that those competitive reactions are strongly dependent on the surface local structure. We investigated how the surface local structure affects those competitive reactions on TiO₂ surface using atomically flat vicinal TiO₂(110) single crystal surface those step-terrace structure was strictly controlled.

Nb doped single-crystal vicinal TiO₂(110)(rutile) surfaces, tilted towards < 001 > and $< \overline{1}10 >$ directions at angles of 0.5 and 2° were used as substrates. The illumination was carried out by use of a 365 nm band from a high-pressure mercury lamp. Fig 1 (a) shows the PL intensity vs. applied potential of TiO₂(110) surfaces tilting in direction at angles of 0.5 and 2°, those terrace width are 10 and 40 nm, respectively. The PL intensity took a maximum near the onset potential of photocurrent, indicating that the PL is arising from surface carrier recombination between conduction-band electrons and the surface-trapped holes. We can see that the PL intensity of the surface with 40nm terrace is larger than that of the surface with 10 nm terrace. Fig. 1(b) shows the PL intensity of the surface tilting in < 001 > and $< \overline{1}10 >$ directions at an angle of 2°. The PL intensity of the surface tilting in $<\overline{1}10>$ direction was larger than that of the surface tilting in < 001 > direction. These results indicate that the PL intensity is strongly dependent on the terrace width and the step direction. The rate of the photoinduced etching reaction (surface roughening reaction) on each surface was also estimated. From those results, we revealed that the 2 kinds of competitive reactions (PL and surface roughening reactions) were strongly affected by the surface local structure of TiO2 surface. These results strongly suggested that the oxidation evolution process (i.e. photocatalytic activity) is also affected by the local structure of the TiO₂ surface.

On the other hand, the surface roughening process induces the change of the surface local structure of TiO_2 (Fig. 2). Considering the fact that the surface local structure of photocatalyst affects the photocatalytic activity, it is quite possible that the photocatalytic reactivity of TiO_2 may be changed by the surface roughening process. We investigated the photocatalytic activity for oxygen photoevolution at the flat and roughened TiO_2 with a focus being placed on the behavior of the onset potential. The results indicated that there is a large difference in the oxygen evolution efficiency between flat and roughened TiO_2 surface. By taking into consideration for the results of Mott-Schottky plot (flat band potential) and I-V curve measurements (onset potential and photocurrent density), it was revealed that such a difference in oxygen evolution efficiency was attributed to the difference in the activation energy of intermediates, induced by the difference of the surface local structure. Interestingly, it was also revealed that the consumption ratio of holes between the 4 kinds of competitive reactions was changed with the progress of the photooxidation reaction. Based on these results, the mechanisms of competitive reactions occurring on TiO_2 surfaces will be discussed.



Fig.1 PL intensity vs. applied potential of vicinal $TiO_2(110)$ surfaces



Fig. 2 AFM images of the atomically flat $n-TiO_2(110)$ surface (a) before and (b) after the UV irradiation, during which the TiO₂ surface was immersed in (b) 0.1 M HClO₄ (pH 1.1).

Acknowledgement

This work was financially supported by JSPS Grant-in-Aid for Scientific Research (B).

References:

[1] Akihito Imanishi, Tomoaki Okamura, Naomichi Ohashi, Ryuhei Nakamura, and Yoshihiro Nakato, *J. Am. Chem. Soc.*, 129(2007)11569.